

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	<b>G05007A</b>	Page.
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TYPE : 6PT902N1T\*\*

CHIP SIZE	0.55 * 0.55 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	51,098 pcs

Maximum Ratings(Ta=25°C)

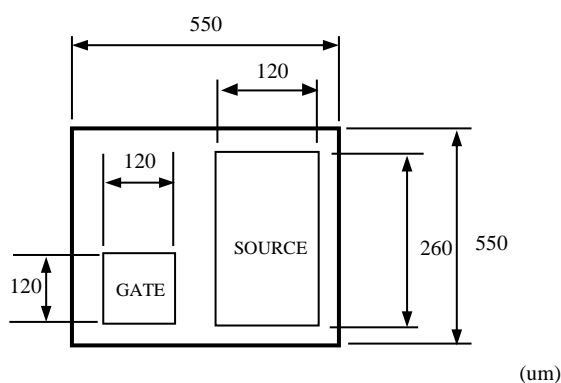
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.5	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS1			±1	uA	VGS=±8V VDS=0V
2	IGSS2			±0.2	uA	VGS=±4.5V VDS=0V
3	IDSS			0.5	uA	VDS=20V VGS=0V
4	BVDSS	22			V	ID=100uA
5	VTH	0.53		1.0	V	ID=250uA
6	RDS(on)1		0.25	0.55	Ω	VGS=4.5V ID=540mA
7	RDS(on)2		0.4	0.7	Ω	VGS=2.5V ID=500mA
8	RDS(on)3		0.65	0.9	Ω	VGS=1.8V ID=350mA
9	VSD	0.5		1.1	V	I=115mA VGS=0V
10	Yfs	200			mS	VDS=10V Id=200mA

※ Built-in ZD between Gate and Source.



NOTE: